

30V N-Channel Enhancement Mode MOSFET

$$V_{DS} (V) = 30V$$

$$I_D = 4 A$$

$$R_{DS(ON)} < 55m\Omega (V_{GS} = 10V)$$

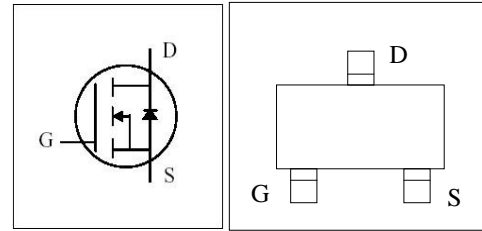
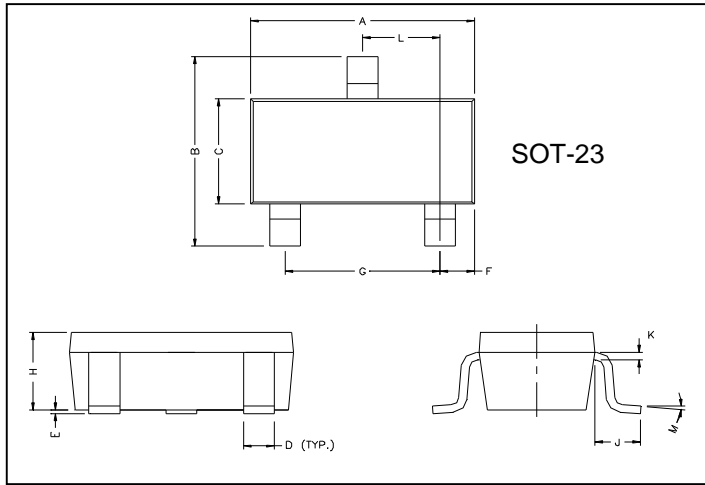
$$R_{DS(ON)} < 70m\Omega (V_{GS} = 4.5V)$$

$$R_{DS(ON)} < 110m\Omega (V_{GS} = 2.5V)$$

Features

The PT3402 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a load switch or in PWM applications.

Package Dimensions



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	2.80	3.00	G	1.80	2.00
B	2.30	2.50	H	0.90	1.1
C	1.20	1.40	K	0.10	0.20
D	0.30	0.50	J	0.35	0.70
E	0	0.10	L	0.92	0.98
F	0.45	0.55	M	0°	10°

Absolute Maximum Ratings $T_A=25^\circ C$ unless otherwise noted				
Parameter	Symbol	Maximum	Units	
Drain-Source Voltage	V_{DS}	30	V	
Gate-Source Voltage	V_{GS}	± 12	V	
Continuous Drain Current ^A	I_D	$T_A=25^\circ C$	4	
		$T_A=70^\circ C$	3.4	
Pulsed Drain Current ^B	I_{DM}	15	A	
Power Dissipation ^A	P_D	$T_A=25^\circ C$	1.4	
		$T_A=70^\circ C$	1	
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	$^\circ C$	

Thermal Characteristics					
Parameter	Symbol	Typ	Max	Units	
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	70	90	$t \leq 10s$	
Maximum Junction-to-Ambient ^A				Steady-State	
Maximum Junction-to-Lead ^C	$R_{\theta JL}$	63	80	Steady-State	

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Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	$I_D=250\mu\text{A}$, $V_{GS}=0\text{V}$	30			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=24\text{V}$, $V_{GS}=0\text{V}$ $T_J=55^\circ\text{C}$			1 5	μA
I_{GSS}	Gate-Body leakage current	$V_{DS}=0\text{V}$, $V_{GS}=\pm 12\text{V}$			100	nA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}$, $I_D=250\mu\text{A}$	0.6	1	1.4	V
$I_{D(ON)}$	On state drain current	$V_{GS}=4.5\text{V}$, $V_{DS}=5\text{V}$	10			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=10\text{V}$, $I_D=4\text{A}$ $T_J=125^\circ\text{C}$		45 66	55 80	$\text{m}\Omega$
		$V_{GS}=4.5\text{V}$, $I_D=3\text{A}$		55	70	$\text{m}\Omega$
		$V_{GS}=2.5\text{V}$, $I_D=2\text{A}$		83	110	$\text{m}\Omega$
g_{FS}	Forward Transconductance	$V_{DS}=5\text{V}$, $I_D=4\text{A}$		8		S
V_{SD}	Diode Forward Voltage	$I_S=1\text{A}$, $V_{GS}=0\text{V}$		0.8	1	V
I_S	Maximum Body-Diode Continuous Current				2.5	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	$V_{GS}=0\text{V}$, $V_{DS}=15\text{V}$, $f=1\text{MHz}$		390		pF
C_{oss}	Output Capacitance			54.5		pF
C_{rss}	Reverse Transfer Capacitance			41		pF
R_g	Gate resistance	$V_{GS}=0\text{V}$, $V_{DS}=0\text{V}$, $f=1\text{MHz}$		3		Ω
SWITCHING PARAMETERS						
Q_g	Total Gate Charge	$V_{GS}=4.5\text{V}$, $V_{DS}=15\text{V}$, $I_D=4\text{A}$		4.34		nC
Q_{gs}	Gate Source Charge			0.6		nC
Q_{gd}	Gate Drain Charge			1.38		nC
$t_{D(on)}$	Turn-On DelayTime	$V_{GS}=10\text{V}$, $V_{DS}=15\text{V}$, $R_L=3.75\Omega$, $R_{GEN}=6\Omega$		3.3		ns
t_r	Turn-On Rise Time			1		ns
$t_{D(off)}$	Turn-Off DelayTime			21.7		ns
t_f	Turn-Off Fall Time			2.1		ns
t_{rr}	Body Diode Reverse Recovery Time	$I_F=4\text{A}$, $dI/dt=100\text{A}/\mu\text{s}$		12		ns
Q_{rr}	Body Diode Reverse Recovery Charge	$I_F=4\text{A}$, $dI/dt=100\text{A}/\mu\text{s}$		6.3		nC

A: The value of $R_{\theta JA}$ is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$. The value in any a given application depends on the user's specific board design. The current rating is based on the $t \leq 10\text{s}$ thermal resistance rating.

B: Repetitive rating, pulse width limited by junction temperature.

C. The $R_{\theta JA}$ is the sum of the thermal impedance from junction to lead $R_{\theta JL}$ and lead to ambient.

D. The static characteristics in Figures 1 to 6,12,14 are obtained using 80 μs pulses, duty cycle 0.5% max.

E. These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$. The SOA curve provides a single pulse rating.

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

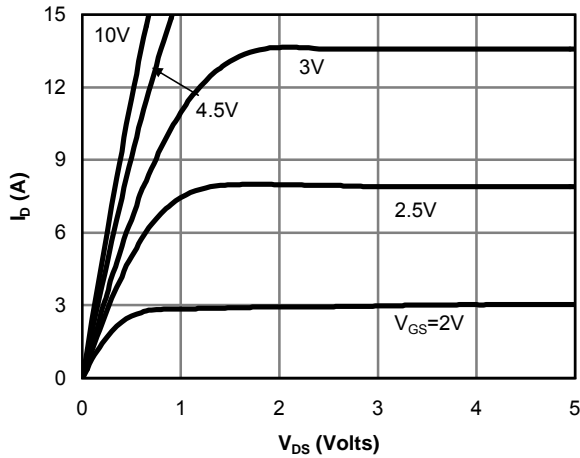


Fig 1: On-Region Characteristics

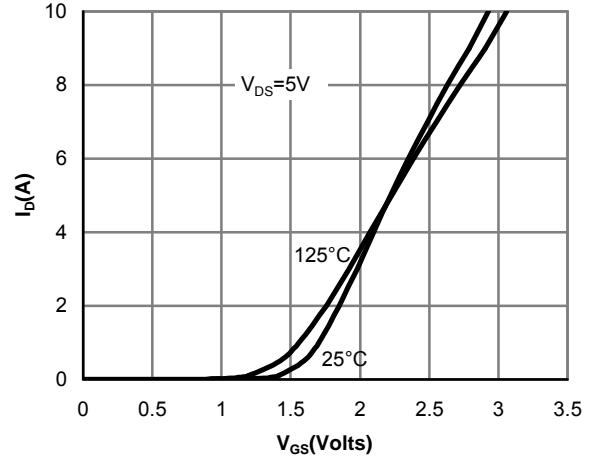


Figure 2: Transfer Characteristics

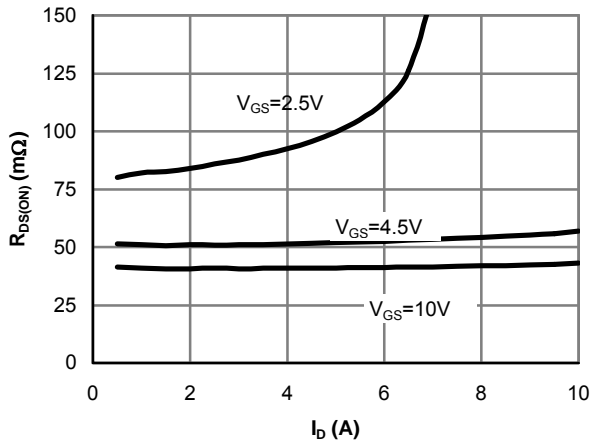


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

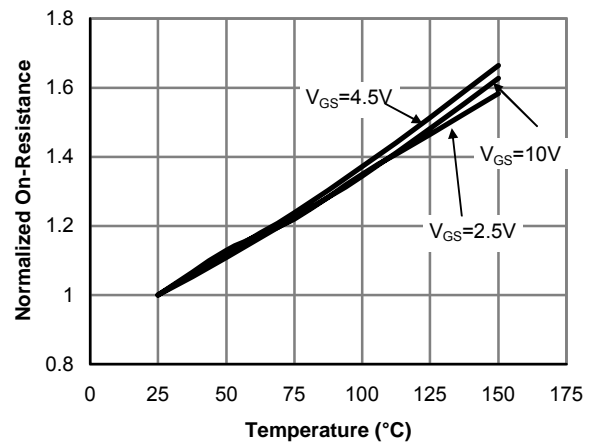


Figure 4: On-Resistance vs. Junction Temperature

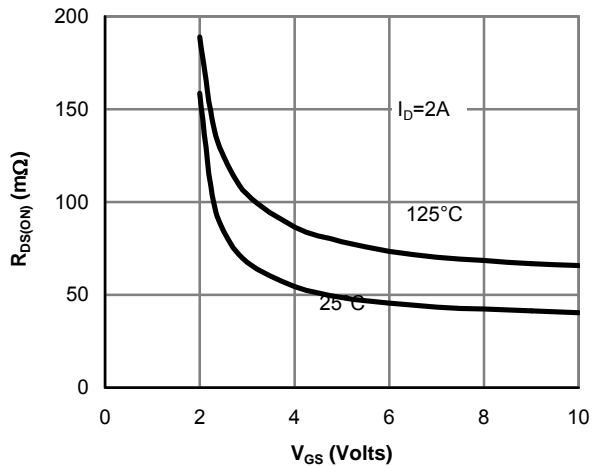


Figure 5: On-Resistance vs. Gate-Source Voltage

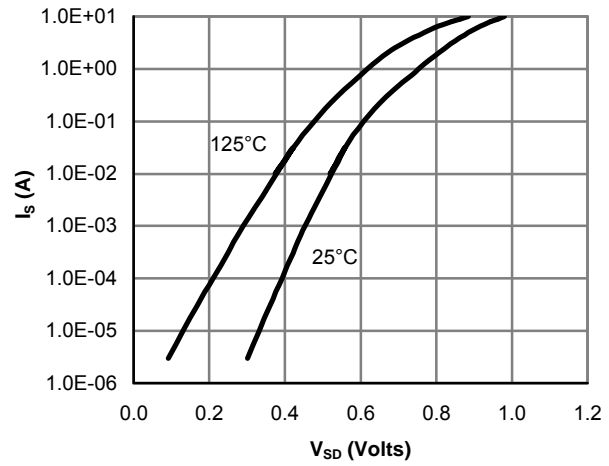


Figure 6: Body-Diode Characteristics

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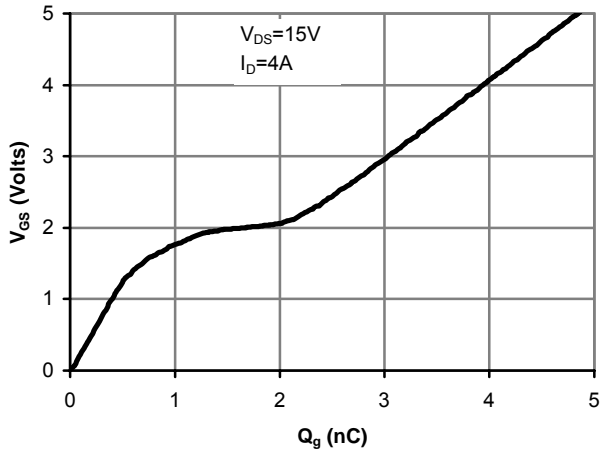


Figure 7: Gate-Charge Characteristics

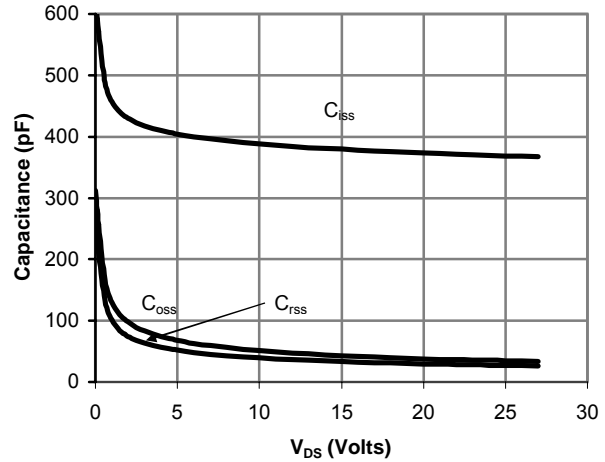


Figure 8: Capacitance Characteristics

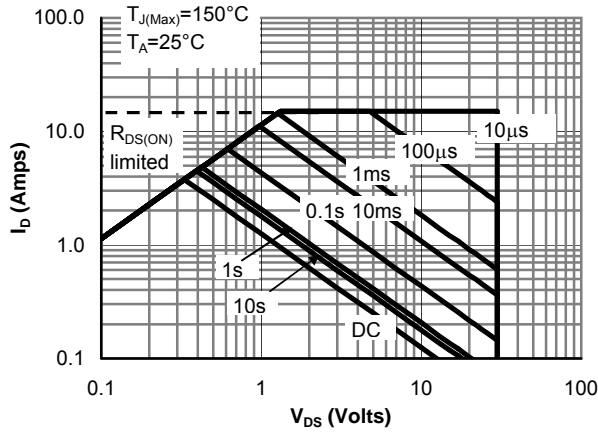


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

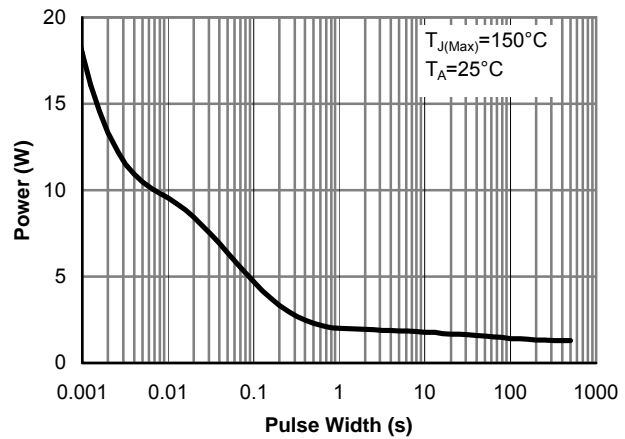


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

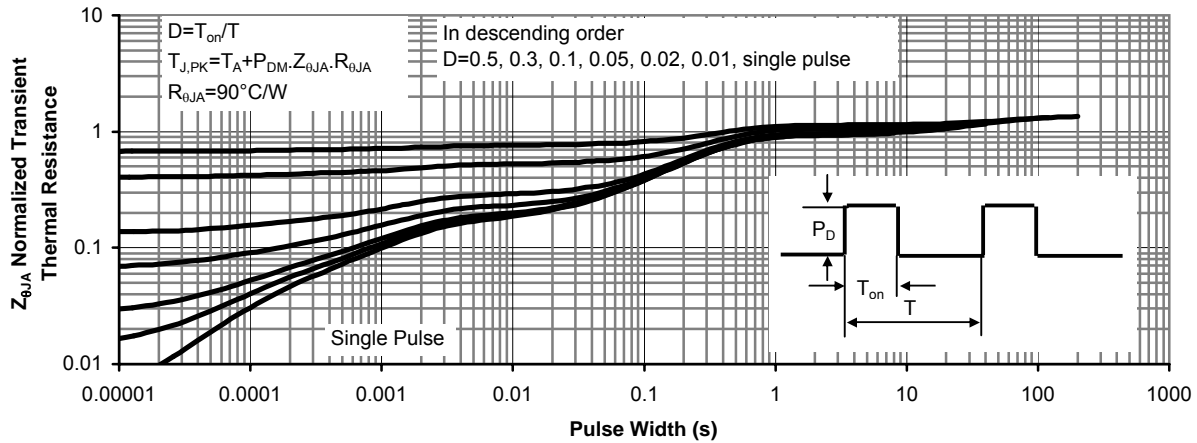


Figure 11: Normalized Maximum Transient Thermal Impedance